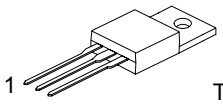
YAREN TECHNOLOGY

75N08

Power MOSFET

80 Amps, 7 5Volts
N-CHANNEL POWER MOSFET



TO-220

*Pb-free plating product number: 75N08

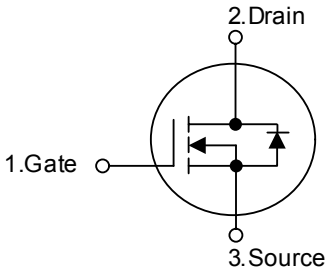
■ DESCRIPTION

This MOSFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

■ FEATURES

- TYPICAL R_{DS}(on) = 0.009Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW THRESHOLD DRIVE

■ SYMBOL



■ ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	75	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	75	V
V_{GS}	Gate- source Voltage	± 20	V
I_D(•)	Drain Current (continuous) at T_C = 25°C	80	A
I_D	Drain Current (continuous) at T_C = 100°C	75	A
I_{DM}(••)	Drain Current (pulsed)	320	A
P_{tot}	Total Dissipation at T_C = 25°C	320	W
	Derating Factor	2	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	20	V/ns
E_{AS} (2)	Single Pulse Avalanche Energy	680	mJ
T_{stg}	Storage Temperature	-55 to 175	°C
T_j	Max. Operating Junction Temperature		

(•) Current limited by package
(••) Pulse width limited by safe operating area.

(1) I_{SD} ≤ 75A, di/dt ≤ 500A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ $T_{JMAX.}$
(2) Starting T_j = 25 ºC, I_D = 40A, V_{DD} = 30V

■ THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	0.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	Typ	300	°C

■ ELECTRICAL CHARACTERISTICS T_C = 25℃ unless otherwise specified

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	75			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating T_C = 125°C			25 25	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	2		4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 40 A V_{GS} = 5 V I_D = 40 A		0.0075 0.0085	0.009 0.010	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	V_{DS} = 20 V I_D = 40		50		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		4300 660 205		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 40 V I_D = 40 A R_G = 4.7 Ω V_{GS} = 4.5 V (Resistive Load, Figure 3)		35 150		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 60V I_D = 80 A V_{GS}= 5V		75 18 31	90	nC nC nC

SWITCHING OFF

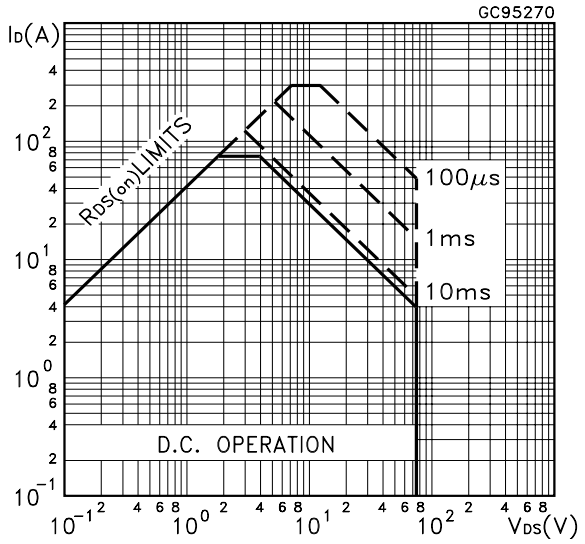
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 40 V I_D = 40 A R_G = 4.7Ω, V_{GS} = 4.5 V (Resistive Load, Figure 3)		110 60		ns ns

SOURCE DRAIN DIODE

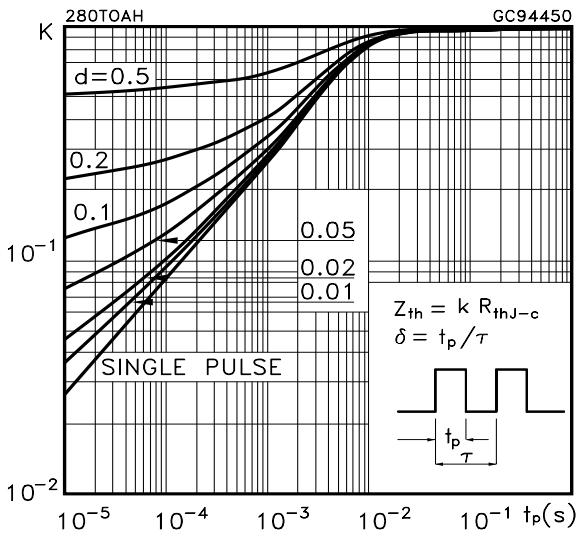
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (•)	Source-drain Current Source-drain Current (pulsed)				80 320	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 80 A V $_{GS}$ = 0			1.4	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 80 Adi/dt = 100A/µs V_{DD} = 20 V T_j = 150°C (see test circuit, Figure 5)		100 380 7.5		ns nC A

(*)Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
(•)Pulse width limited by safe operating area.

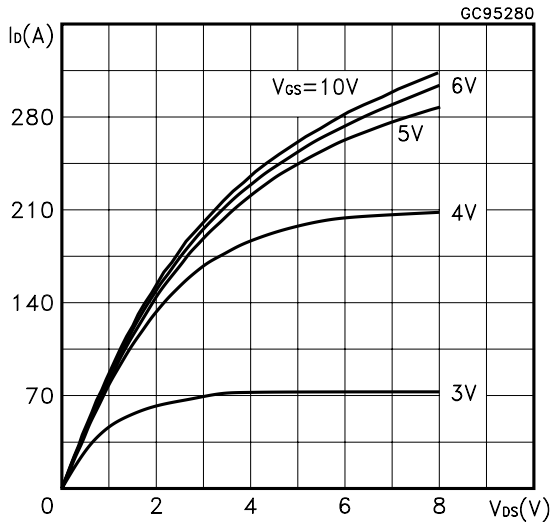
Safe Operating Area



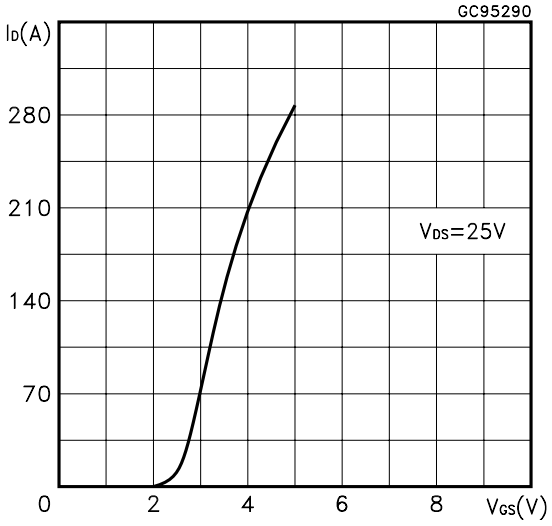
Thermal Impedance



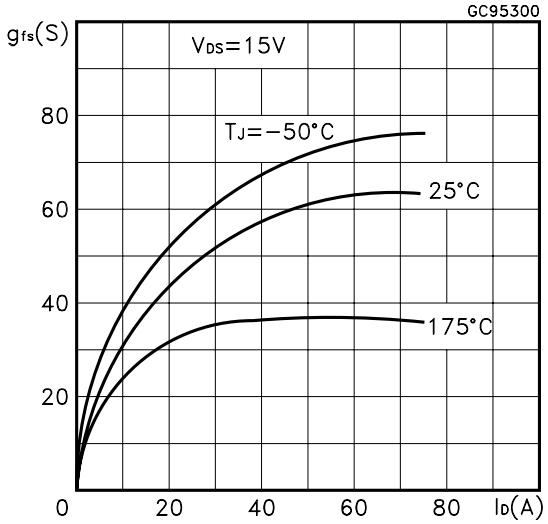
Output Characteristics



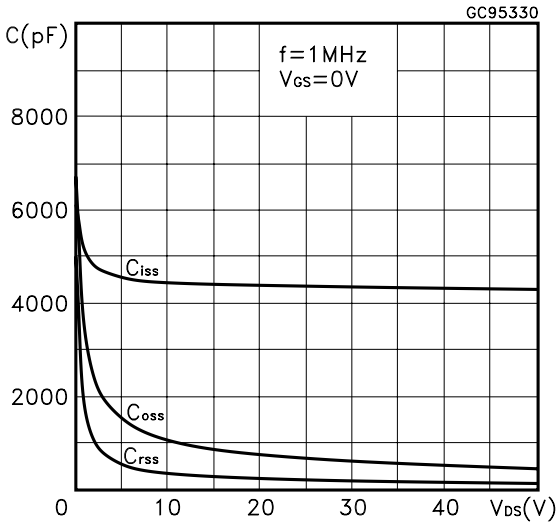
Transfer Characteristics



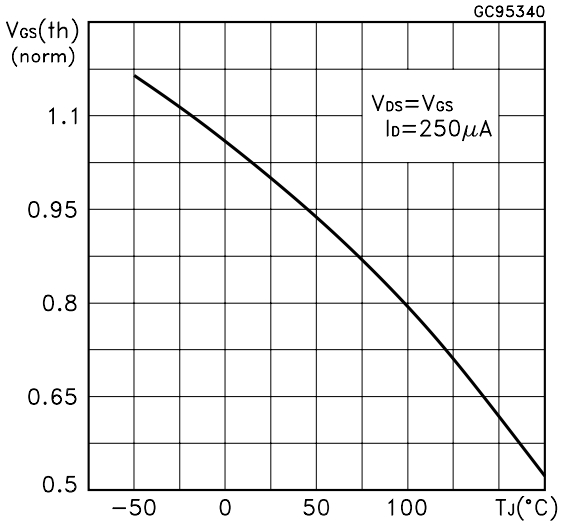
Transconductance



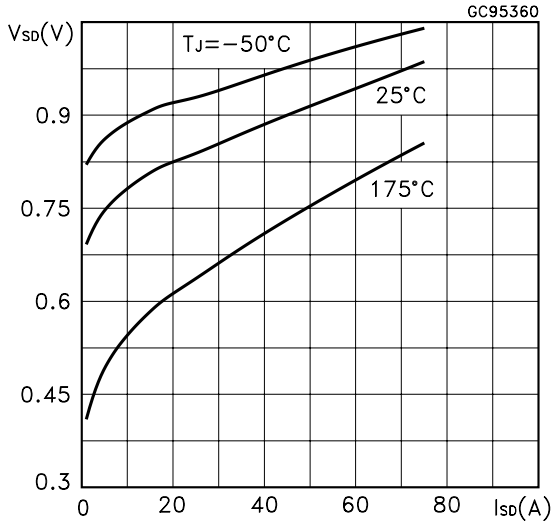
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature.